

MOS Transistor Parameter Analyzer

This MOS transistor parameter analyzer measures threshold voltage $U_{GS(th)}$, internal resistance RDS, transconductance gm, and withstand voltage $V(BR)_{DS}$. Test ranges include $U_{GS(th)}$: 0.1~9.9V, RDS: 0.001~9.999 Ω , gm: 0.10~10.00S, $V(BR)_{DS}$: 50~650V.



Overview

Precision MOS Transistor Analysis

The MOS Transistor Parameter Analyzer is a precision instrument engineered for the accurate testing and selection of MOS transistors in research, development, and quality control environments. It features continuous test current adjustment to simulate various working conditions and provides real-time monitoring of critical parameters. With advanced testing capabilities for high-current RDS evaluation, this device ensures component reliability and optimal performance matching.

Measurement Capabilities

Parameter Test Ranges

Parameter	Range
Threshold Voltage ($U_{GS(th)}$)	0.1 - 9.9 V
Internal Resistance (RDS)	0.001 - 9.999 Ω
Transconductance (gm)	0.10 - 10.00 S
Withstand Voltage ($V(BR)_{DS}$)	50 - 650 V

Measured Parameters

Threshold Voltage ($U_{GS(th)}$), Internal Resistance (RDS), Transconductance (gm), Withstand Voltage ($V(BR)_{DS}$)

Operational Features

Test Current Range

0.1 A

Min Current

5 A

Max Current

Key Operational Features

- Continuously adjustable test current for simulation of different working situations
- Freely set judging limits and grouping values
- Automatic alarm system when measured values exceed limits
- Advanced high-current RDS testing technology